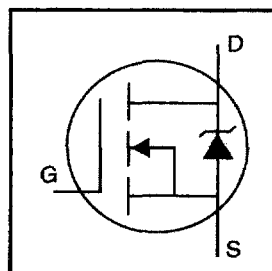


IRL2505S/L

HEXFET® Power MOSFET

- Logic-Level Gate Drive
- Advanced Process Technology
- Surface Mount (IRL2505S)
- Low-profile through-hole (IRL2505L)
- 175°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated



$$V_{DSS} = 55V$$

$$R_{DS(on)} = 0.008\Omega$$

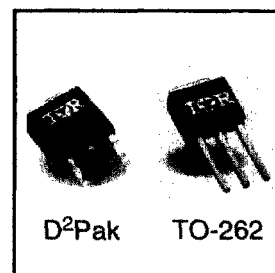
$$I_D = 104A^{\circ}$$

Description

Fifth Generation HEXFET® Power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design for which HEXFET Power MOSFETs are well known, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D²Pak is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²Pak is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.

The through-hole version (IRL2505L) is available for low-profile applications.



D²Pak

TO-262

Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{\circ}$	104 ^⑥	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^{\circ}$	74	
I_{DM}	Pulsed Drain Current ①⑤	360	
$P_D @ T_A = 25^\circ C$	Power Dissipation	3.8	W
$P_D @ T_C = 25^\circ C$	Power Dissipation	200	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy ②⑤	500	mJ
I_{AR}	Avalanche Current ①	54	A
E_{AR}	Repetitive Avalanche Energy ①	20	mJ
dv/dt	Peak Diode Recovery dv/dt ③⑥	5.0	V/ns
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
		300 (1.6mm from case)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	0.75	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mounted, steady-state)**	—	40	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.035	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1mA$ ⑤
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.008	Ω	$V_{GS} = 10V, I_D = 54A$ ④
		—	—	0.010		$V_{GS} = 5.0V, I_D = 54A$ ④
		—	—	0.013		$V_{GS} = 4.0V, I_D = 45A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	59	—	—	S	$V_{DS} = 25V, I_D = 54A$ ⑤
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	A	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 44V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	130	nC	$I_D = 54A$
Q_{gs}	Gate-to-Source Charge	—	—	25		$V_{DS} = 44V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	67		$V_{GS} = 5.0V$, see figure 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	12	—	ns	$V_{DD} = 28V$
t_r	Rise Time	—	160	—		$I_D = 54A$
$t_{d(off)}$	Turn-Off Delay Time	—	43	—		$R_G = 1.3\Omega, V_{GS} = 5.0V$
t_f	Fall Time	—	84	—		$R_D = 0.50\Omega$, see figure 10 ④⑤
L_S	Internal Source Inductance	—	7.5	—	nH	Between lead, and center of die contact
C_{iss}	Input Capacitance	—	5000	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	1100	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	390	—		$f = 1.0MHz$, see figure 5 ⑤

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	104⑥	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	360		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 54A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	140	210	ns	$T_J = 25^\circ\text{C}, I_F = 54A$
Q_{rr}	Reverse Recovery Charge	—	650	970	nC	$di/dt = 100A/\mu s$ ④⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (see figure 11)
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 240\mu H$, $R_G = 25\Omega$, $I_{AS} = 54A$. (see figure 12)
- ③ $I_{SD} \leq 54A$, $di/dt \leq 230A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$
- ⑤ Uses IRL2505 data and test conditions

⑥ Calculated continuous current based on maximum allowable junction temperature; for recommended current-handling of the package refer to Design Tip # 93-4

** When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

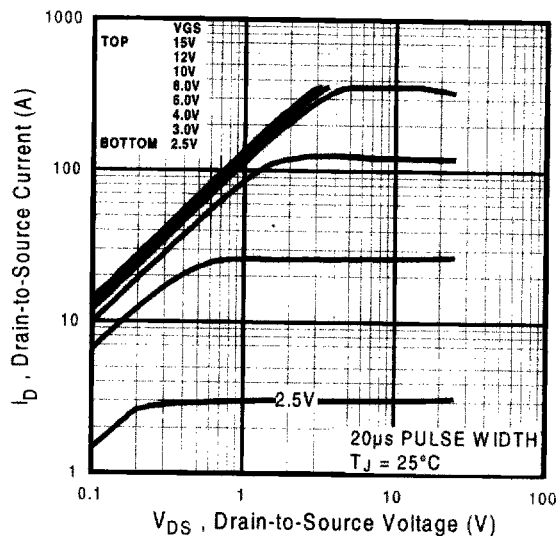


Fig 1. Typical Output Characteristics

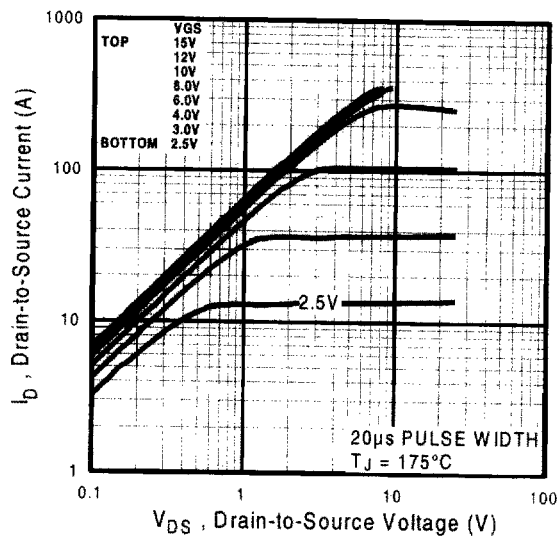


Fig 2. Typical Output Characteristics

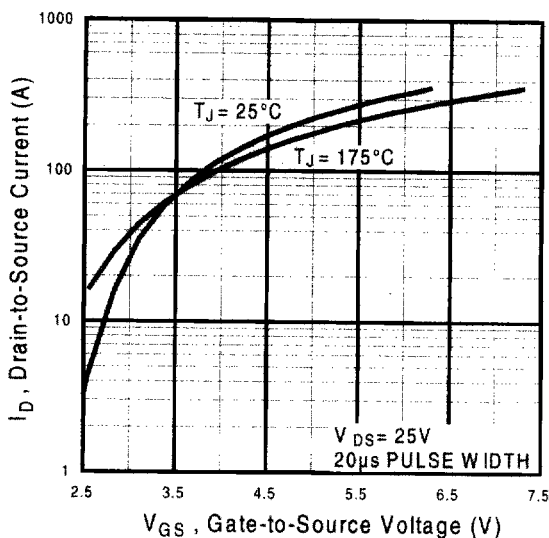


Fig 3. Typical Transfer Characteristics

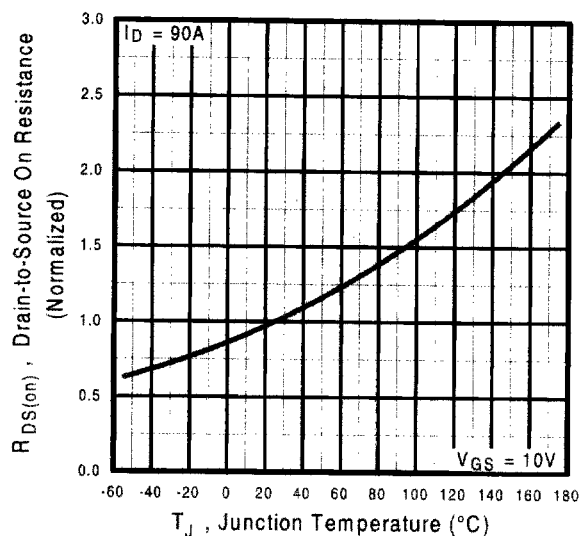


Fig 4. Normalized On-Resistance
Vs. Temperature

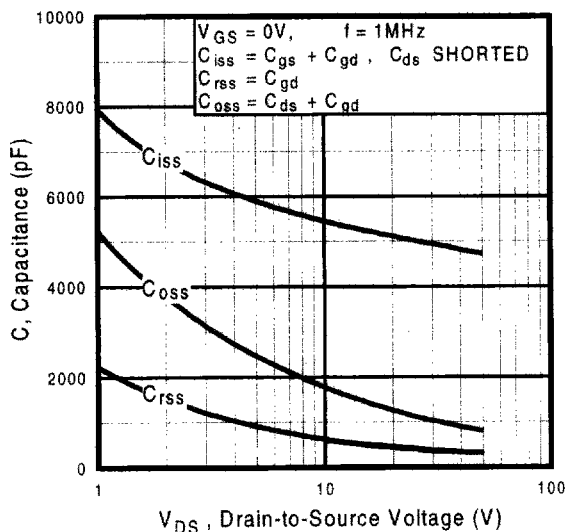


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

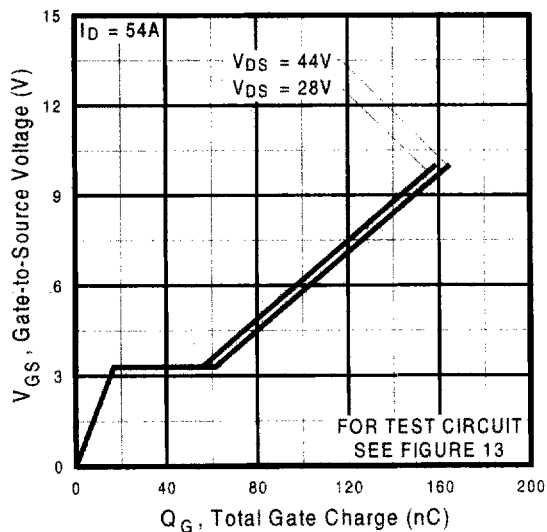


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

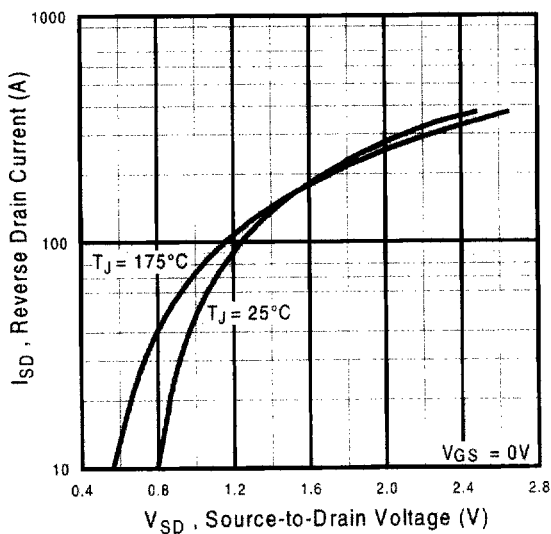


Fig 7. Typical Source-Drain Diode Forward Voltage

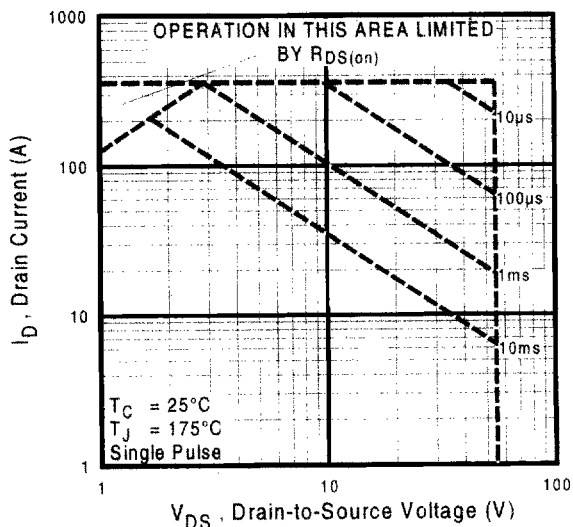


Fig 8. Maximum Safe Operating Area

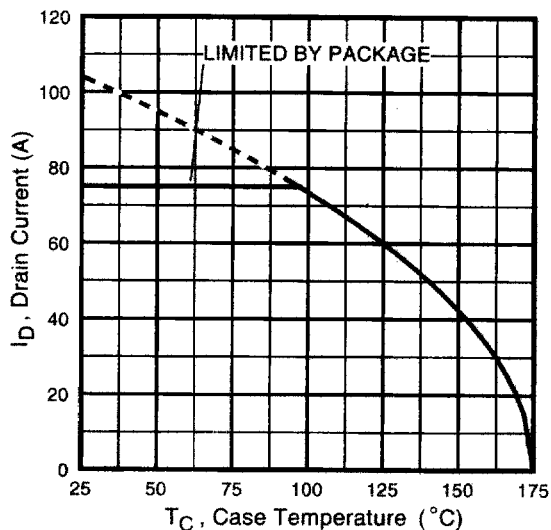


Fig 9. Maximum Drain Current Vs. Case Temperature

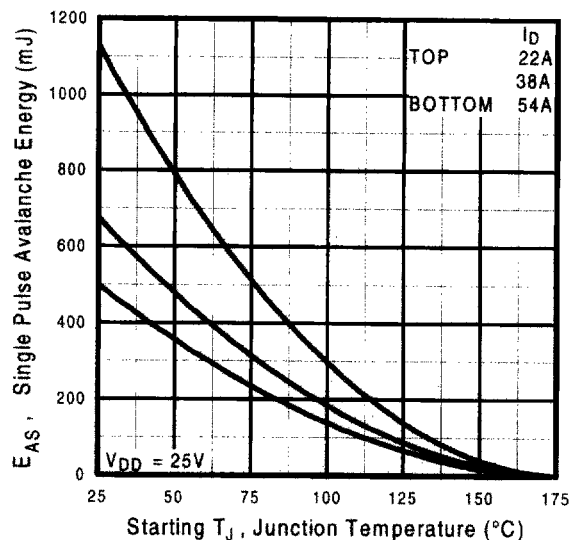


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

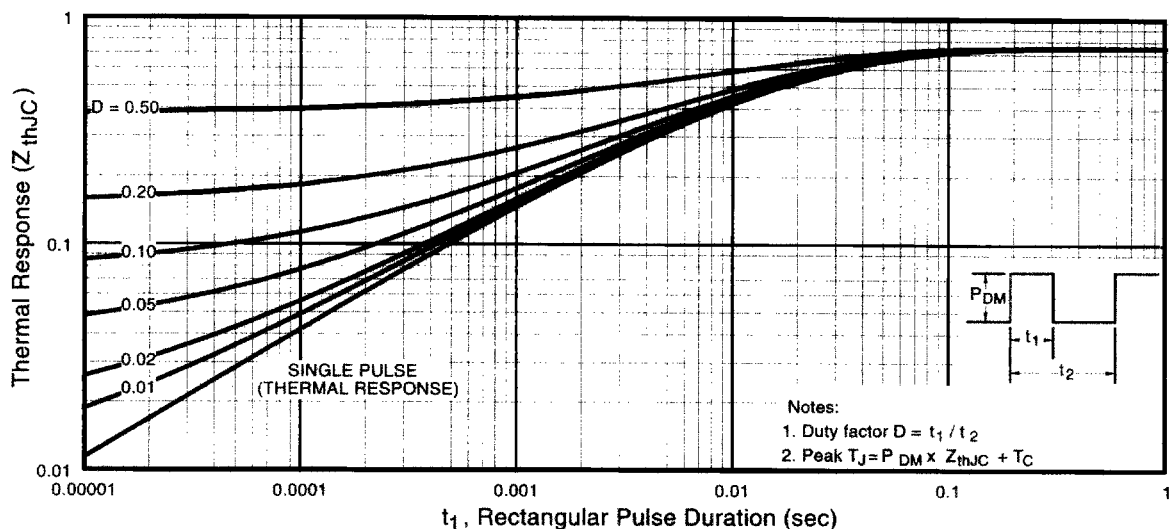


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

Mechanical drawings, Appendix A
Part marking information, Appendix B
Test Circuit diagrams, Appendix C